

Application No. 09/497,508

Polycrystalline silicon film containing Ni

1/7/02

East Search					
Search	L No.	Hits	Text Search		Data Bases
BRS	L5	47	conductivity adj activation adj energy	1/7/02 9:44	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L6	36	5 and ev	1/7/02 9:45	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L7	33	6 and @ay<1999	1/7/02 10:34	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L8	10	7 and (ni nickel)	1/7/02 10:37	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
BRS	L9	8	8 and (si silicon)	1/7/02 10:37	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB

Search Result

USPAT	Date	Page	Title	Cl/Sub	Cl/Sub	Inventor
US 5994164 A	19991130	19	Nanostructure tailoring of material properties using controlled crystallization	438/97	438/162 ; 438/166 ; 438/486 ; 438/487 ; 438/488	Fonash, Stephen J. , et al.
US 4509066 A	19850402	5	Sputtered semiconducting films of catenated phosphorus material and devices formed therefrom	257/52	204/192.25 ; 257/289 ; 257/471 ; 428/426 ; 428/432 ; 428/620 ; 428/938	Schachter, Rozalie , et al.
US 4226898 A	19801007	20	Amorphous semiconductors equivalent to crystalline semiconductors produced by a glow discharge process	438/483	136/258 ; 148/DIG.61 ; 427/578 ; 430/136 ; 430/84 ; 438/485 ; 438/93 ; 438/96	Ovshinsky, Stanford R. , et al.
US 4099071 A	19780704	8	Monolithic electronic scanning device	327/365	257/467 ; 324/106 ; 338/217	Thornburg, David D.
US 5994164 A	19991130	19	Nanostructure tailoring of material properties using controlled crystallization	438/97	438/162 ; 438/166 ; 438/486 ; 438/487 ; 438/488	Fonash, Stephen J. , et al.
US 5509189 A	19960423	20	Method for making an electrochemical cell	29/623.1	117/103 ; 117/108 ; 117/940 ; 117/947 ; 216/94 ; 264/109 ; 419/10 ; 419/19 ; 419/61 ; 427/115 ; 427/126.3 ; 427/126.5 ; 427/248.1 ; 427/77	Tuller, Harry L. , et al.